Tunable IMN and OMN

For proper operation of the DPA the inputs of the carrier and peaking amplifiers must be 90° out of phase. 90° phase shift is realized with a λ/4 transformer ether in micro strip or lumped element depending on the operating frequency. It is obvious that this presents a challenge if large bandwidth is desired. To solve this problem reconfigurable input and output matching networks (IMN/OMN) are proposed. To achieve reconfigurable matching networks microelectromechanical systems (MEMS) are used. MEMS devices are preferred due to their ultra-linearity, low losses, and easy of integration in current MMIC processes [1]. A reconfigurable matching network can present the optimum impedances to both input and output of the transistor for the best gain and efficiency at various operating frequencies. As shown in [1] such topology yielded high power gains and efficiency at 1.7,2.14 and 2.6GHz using the same amplifier with reconfigurable matching networks.

